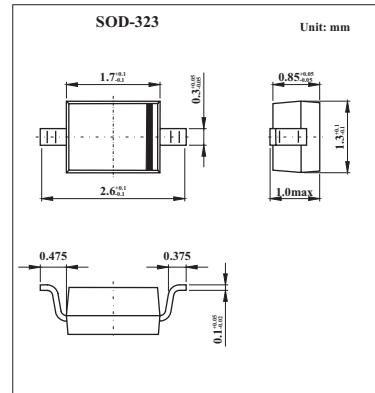


BAS140WS

■ Features

- General purpose diodes for high-speed switching
- Circuit protection
- Voltage clamping
- High-level detecting and mixing



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	40	V
Forward current	I _F	120	mA
Surge forward current t ≤ 1.0 μ s	I _{FSM}	200	mA
Total power dissipation Ts ≤ 113 °C	P _{tot}	250	mW
Operating temperature range	T _{op}	-55 to +125	°C
Storage Temperature range	T _{stg}	-65 to +150	°C
Junction ambient ⁽¹⁾	R _{thJA}	≤ 260	K/W
Junction- soldering point	R _{thJS}	≤ 150	K/W

Note:

1. Package mounted on an epoxy pcb 40 mm × 40 mm × 15 mm/1cm² Cu.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Min	Typ	Max	Unit
Breakdown voltage I _(BR) = 10 μ A	V _(BR)	40			V
Forward voltage I _F = 1 mA	V _F				mV
I _F = 10 mA		250	310	380	
I _F = 15 mA		350	450	500	
Reverse current V _R = 30 V		600	720	1000	
V _R = 40 V	I _R			1	μ A
Diode capacitance V _R = 0; f = 1 MHz	C _T		3	5	
Differential forward resistance I _F = 10 mA, f = 10 KHz	R _F		10		Ω
Series inductance	L _s		2		nH

■ Marking

Marking	4
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